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NTE5800 thru NTE5809
Axial Lead Standard Recovery
Silicon Rectifiers, 3 Amp, DO–201AD

Description:

The NTE5800 through NTE5809 silicon rectifiers are designed for use in power supplies and other applications having need of a device with the following features:

Features:

- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified. Single Phase, half wave, 60Hz, relative or inductive load. For capacitive load, derate current by 20%)

Peak Repetitive Reverse Voltage, V_{RRM}
Working Peak Reverse Voltage, V_{RWM}
DC Blocking Voltage, V_R

NTE5800	50V
NTE5801	100V
NTE5802	200V
NTE5803	300V
NTE5804	400V
NTE5805	500V
NTE5806	600V
NTE5808	800V
NTE5809	1000V

Maximum RMS Reverse Voltage, $V_{R(RMS)}$

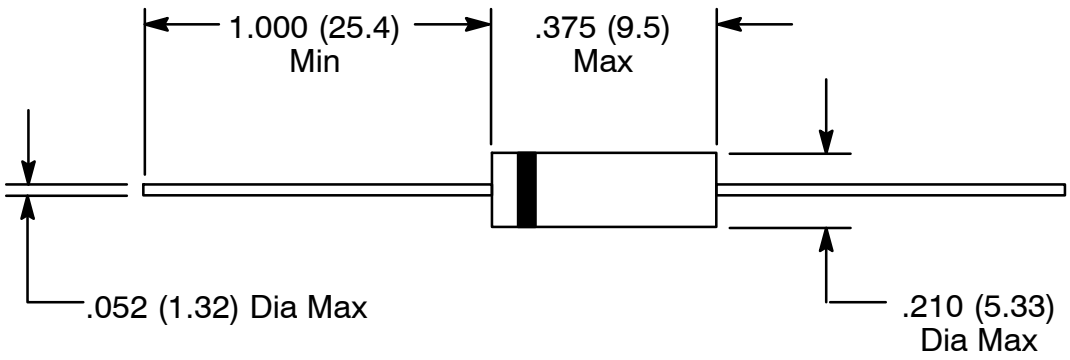
NTE5800	35V
NTE5801	70V
NTE5802	140V
NTE5803	210V
NTE5804	280V
NTE5805	350V
NTE5806	420V
NTE5808	560V
NTE5809	700V

Average Rectified Current (T_A = +75°C Note 1), I_O 3A
Peak Forward Surge Current, I_{FSM}
(Superimposed on a Rated Load, 8.3ms Single Half–Sine Wave) 200A
Operating Junction Temperature Range, T_J . . . . . –65° to +125°C
Storage Temperature Range, T_{stg} . . . . . –65° to +150°C
Thermal Resistance, Junction–to–Ambient (Note 1), R_{thJA} . . . . . +20°C/W

Note 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

Electrical Characteristics: (T_A = +25°C unless otherwise specified. Single Phase, half wave, 60Hz, relative or inductive load. For capacitive load, derate current by 20%)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Peak Reverse Current	I_{RM}	Rated DC Blocking Voltage	T_A = +25°C	–	–	5.0	μA
			T_A = +100°C	–	–	100	μA
Maximum Forward Voltage	V_{FM}	i_F = 3A		–	–	1.0	V
Junction Capacitance		V_R = 4V, f = 1MHz		–	30	–	pF



Color Band Denotes Cathode